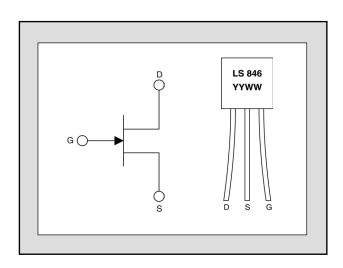
# LINEAR SYSTEMS

#### Linear Integrated Systems

FEATURES					
ULTRA LOW NOISE	e <sub>n</sub> = 3nV/√Hz				
LOW GATE LEAKAGE I <sub>G</sub> = 15pA					
ABSOLUTE MAXIMUM RATINGS <sup>1</sup>					
@ 25 °C (unless otherwise stated)					
Maximum Temperatures					
Storage Temperature	-65 to +150 °C				
Operating Junction Temperature	-55 to +135 °C				
Maximum Power Dissipation					
Continuous Power Dissipation @ +125 °C	350mW				
Maximum Currents					
Gate Forward Current	$I_{G(F)} = 50 \text{mA}$				
Maximum Voltages					
Drain to Source	$V_{DSO} = 60V$				
Gate to Source	$V_{GSS} = 60V$				
Gate to Drain	$V_{GDS}$ = 60V				

# LS846

### LOW NOISE, LOW LEAKAGE SINGLE N-CHANNEL JFET



\*For equivalent monolithic dual, see LS843 family.

#### ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS	
BV <sub>GSS</sub>	Gate to Source Breakdown Voltage	60			V	V <sub>DS</sub> = 0, I <sub>D</sub> = 1nA	
V <sub>GS(OFF)</sub>	Gate to Source Pinch-off Voltage	1		3.5	V	V <sub>DS</sub> = 15V, I <sub>D</sub> = 1nA	
$V_{GS}$	Gate to Source Operating Voltage	0.5		3.5	V	V <sub>DS</sub> = 15V, I <sub>D</sub> = 500µA	
I <sub>DSS</sub>	Drain to Source Saturation Current	1.5	5	15	mA	V <sub>DG</sub> = 15V, V <sub>GS</sub> = 0	
l <sub>G</sub>	Gate Operating Current		15	50	pА	V <sub>DG</sub> = 15V, I <sub>D</sub> = 500µA	
l <sub>G</sub>	Gate Operating Current Reduced V <sub>DG</sub>		5	30	pА	V <sub>DG</sub> = 3V, I <sub>D</sub> = 500µA	
I <sub>GSS</sub>	Gate to Source Leakage Current			100	pА	V <sub>DG</sub> = 15V, V <sub>DS</sub> = 0	
Y <sub>fss</sub>	Full Conductance Transconductance	1500			µmho	V <sub>GD</sub> = 15V, V <sub>GS</sub> = 0, <i>f</i> = 1kHz	
Y <sub>fs</sub>	Typical Conductance Transconductance	1000	1500		µmho	V <sub>DG</sub> = 15V, I <sub>D</sub> = 500µA	
Y <sub>oss</sub>	Full Output Conductance			20	µmho	V <sub>DG</sub> = 15V, V <sub>GS</sub> = 0	
Y <sub>os</sub>	Typical Output Conductance		0.2	2	µmho	V <sub>DG</sub> = 15V, I <sub>D</sub> = 500µA	
NF	Noise Figure			0.5	dB	$V_{DS} = 15V, V_{GS} = 0, R_G = 10M\Omega, f = 100Hz, NBW = 6Hz$	
en	Noise Voltage		3	7	nV/√Hz	V <sub>DS</sub> = 15V, I <sub>D</sub> = 500µA, <i>f</i> = 1kHz, NBW = 1Hz	
en	Noise Voltage			11	nV/√Hz	V <sub>DS</sub> = 15V, I <sub>D</sub> = 500µA, <i>f</i> = 10Hz, NBW = 1Hz	
CISS	Common Source Input Capacitance			8	pF	V <sub>DS</sub> = 15V, I <sub>D</sub> = 500μA	
C <sub>RSS</sub>	Common Source Reverse Transfer Cap.			3	pF		

1. Absolute maximum ratings are limiting values above which serviceability may be impaired.

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